FAX TRANSMISSION

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CONTENTS: Attached are our proposed claim amendments (not for entry). We look forward to our Interview on Tuesday, February 23, 2010 at 10:00AM.

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PROPOSED CLAIM AMENDMENTS – NOT FOR ENTRY

1. (Currently Amended) An InP substrate for epitaxial growth,

wherein, when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of the InP substrate, by intensity of the incident light from the light source, the light source having a wavelength of 488 nm, and wherein the InP substrate comprises:

the haze [[is]] of not more than 1 ppm all over an effectively used area having at least two inches of the InP substrate; and

an off-angle with respect to a plane direction is 0.05 to 0.10°, wherein the effectively used area includes the surface area of the substrate, with the exception of the peripheral part including the chamfered part of the substrate.

2. (Cancelled)

3. (Cancelled)

4. (Previously Presented) The InP substrate as claimed in claim 1, wherein a dislocation density is not more than $1000/cm^2$.

5. (Previously Presented) The InP substrate as claimed in claim 4, wherein the dislocation density is not more than $500/cm^2$.

6. (Previously Presented) A compound semiconductor substrate for epitaxial growth, comprising an InP substrate and at least one epitaxial layer on the InP substrate, wherein:

the InP substrate has an off-angle with respect to a plane direction of 0.05 to 0.10°,

the InP substrate has a haze of 0.5 to 0.8 ppm, and

the haze in a surface of the at least one epitaxial layer is not more than 1 ppm,

wherein haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto the surface of the at least one epitaxial layer or a surface of the InP substrate, by intensity of the incident light from the light source.

7. (Previously Presented) An InP substrate for epitaxial growth,

wherein, when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of the InP substrate, by intensity of the incident light from the light source,

the haze is not more than 1 ppm all over an effectively used area of the InP substrate, and

an off-angle with respect to a plane direction is 0.05 to 0.10° .

8. (New) An InP substrate for epitaxial growth, comprising an off-angle with respect to a plane direction of 0.05 to 0.10°, and wherein a manufacturing method of the InP substrate comprises:

performing a mirror polishing on a surface of the InP substrate; and

SECOND SET OF PROPOSED CLAIM AMENDMENTS – NOT FOR ENTRY

1. (Currently Amended) An InP substrate for epitaxial growth having haze of not more than 1 ppm in an entirety of an effectively used area of the substrate, and further having an off-angle with respect to a plane direction is 0.05 to 0.10°, wherein:

~~wherein, when~~ haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of the InP substrate, by intensity of the incident light from the light source, the light source having a wavelength of 488 nm,

~~the haze is not more than 1 ppm all over an effectively used area of the InP substrate and an off-angle with respect to a plane direction is 0.05 to 0.10°, wherein~~ the effectively used area of the wafer includes the entirety of a surface area of the substrate, with the exception of [[the]] a peripheral part including [[the]] a chamfered part of the substrate, and is at least two inches in diameter.

2. (Cancelled)

3. (Cancelled)

4. (Previously Presented) The InP substrate as claimed in claim 1, wherein a dislocation density is not more than 1000/cm^2.

5. (Previously Presented) The InP substrate as claimed in claim 4, wherein the dislocation density is not more than $500/cm^2$.

6. (Previously Presented) A compound semiconductor substrate for epitaxial growth, comprising an InP substrate and at least one epitaxial layer on the InP substrate, wherein:

the InP substrate has an off-angle with respect to a plane direction of 0.05 to 0.10°,

the InP substrate has a haze of 0.5 to 0.8 ppm, and

the haze in a surface of the at least one epitaxial layer is not more than 1 ppm,

wherein haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto the surface of the at least one epitaxial layer or a surface of the InP substrate, by intensity of the incident light from the light source.

7. (Previously Presented) An InP substrate for epitaxial growth,

wherein, when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of the InP substrate, by intensity of the incident light from the light source,

the haze is not more than 1 ppm all over an effectively used area of the InP substrate, and

an off-angle with respect to a plane direction is 0.05 to 0.10° .

8. (New) An InP substrate for epitaxial growth having an off-angle with respect to a plane direction of 0.05 to 0.10°, wherein the InP substrate is manufactured by:

performing mirror polishing on a surface of the InP substrate; and

selecting the substrate only if it has a haze of not more than 1 ppm in an entirety of an effectively used area of the substrate,

wherein the effectively used area of the substrate is at least two inches in diameter.

9. (New) A manufacturing method of an InP substrate comprising:

performing mirror polishing on a surface of the InP substrate; and

selecting the substrate only if it has both (i) a haze of not more than 1 ppm in an entirety of an effectively used area of the substrate, and (ii) an off-angle with respect to a plane direction of 0.05 to 0.10°,

wherein the effectively used area of the substrate is at least two inches in diameter.

10. (New) A method to reduce haze on a surface of an epitaxial layer grown on an InP substrate, comprising epitaxially growing a semiconductor layer on the InP substrate according to claim 1.

11. (New) A semiconductor device comprising:

the InP substrate for epitaxial growth according to claim 1; and

a semiconductor layer which is epitaxially grown on the InP substrate.

12. (New) A method to perform an epitaxial growth, comprising epitaxially growing a semiconductor layer on the InP substrate according to claim 1.